



# STD9NM40N, STP9NM40N

N-channel 400 V, 0.73  $\Omega$  typ., 5.6 A MDmesh™ II Power MOSFET  
in DPAK and TO-220 packages

Datasheet — production data

## Features

Order codes	$V_{DSS}@T_{JMAX}$	$R_{DS(on)max.}$	$I_D$
STD9NM40N	450 V	< 0.79 $\Omega$	5.6 A
STP9NM40N			

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

## Applications

- Switching applications

## Description

These devices are N-channel Power MOSFETs developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

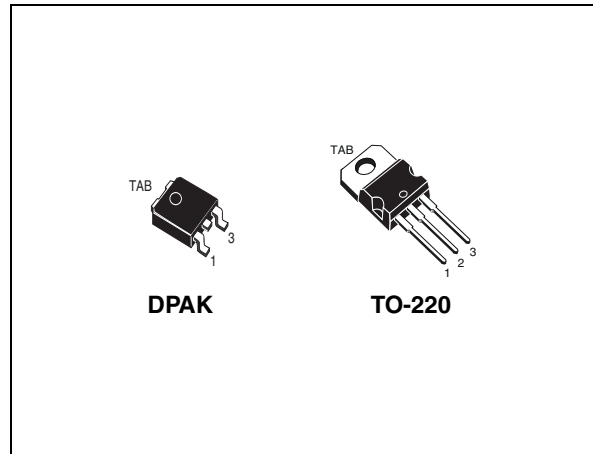


Figure 1. Internal schematic diagram

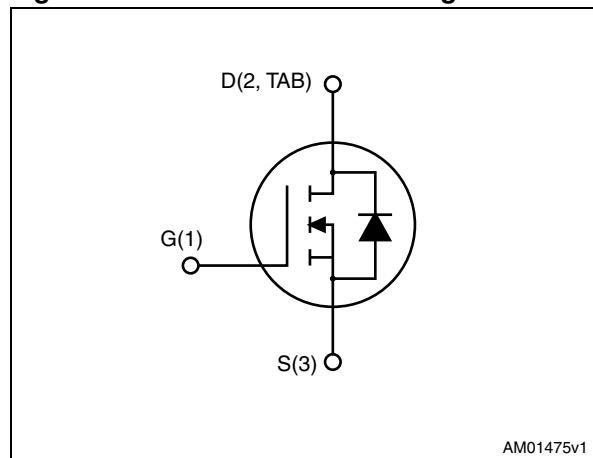


Table 1. Device summary

Order codes	Marking	Packages	Packaging
STD9NM40N	9NM40N	DPAK	Tape and reel
STP9NM40N		TO-220	Tube

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	400	V
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	5.6	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	4.3	A
$I_{DM}^{(1)}$	Drain current (pulsed)	22.4	
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	60	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	40	V/ns
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2.  $I_{SD} \leq 5.6\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{Peak} < V_{(BR)DSS}$ ,  $V_{DS} = 80\% V_{(BR)DSS}$

**Table 3. Thermal data**

Symbol	Parameter	Value		Unit
		DPAK	TO-220	
$R_{thj-case}$	Thermal resistance junction-case max	2.08		$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max	50		$^\circ\text{C}/\text{W}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	2	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	140	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ( $V_{GS} = 0$ )	$I_D = 1\text{ mA}$	400			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 400\text{ V}$ $V_{DS} = 400\text{ V}, T_C = 125\text{ °C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$		0.73	0.79	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 50\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	365	-	pF
$C_{oss}$	Output capacitance			30		
$C_{rss}$	Reverse transfer capacitance			2.3		
$C_{oss(eq)}^{(1)}$	Equivalent output capacitance time related	$V_{DS} = 0\text{ to }50\text{ V}, V_{GS} = 0$	-	147.5	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}, I_D = 0$	-	5.4	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 320\text{ V}, I_D = 5.6\text{ A},$ $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 17</a> )	-	14	-	nC
$Q_{gs}$	Gate-source charge			3		
$Q_{gd}$	Gate-drain charge			7		

1.  $C_{oss\ eq}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit	
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 200\text{ V}$ , $I_D = 5.6\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 16</a> )		7		ns	
$t_r$	Rise time			4.4		ns	
$t_{d(off)}$	Turn-off-delay time				25		ns
$t_f$	Fall time				8.8		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				5.6	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				22.4	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 5.6\text{ A}$ , $V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 5.6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 21</a> )		187		ns
$Q_{rr}$	Reverse recovery charge			1.3		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current				14	A
$t_{rr}$	Reverse recovery time	$I_{SD} = 5.6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 21</a> )		224		ns
$Q_{rr}$	Reverse recovery charge			1.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current				13	A

1. Pulse width limited by safe operating area.

2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for DPAK

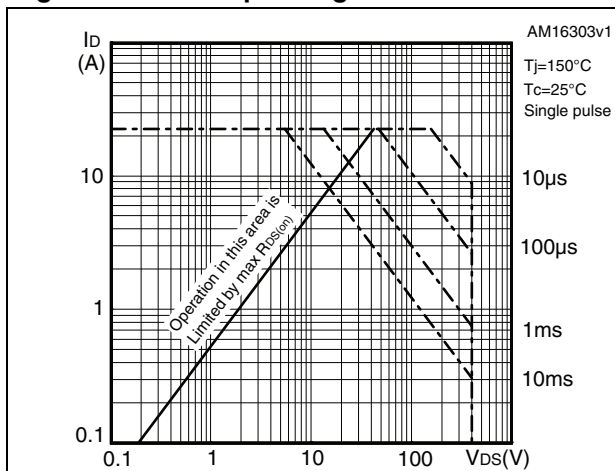


Figure 3. Thermal impedance for DPAK

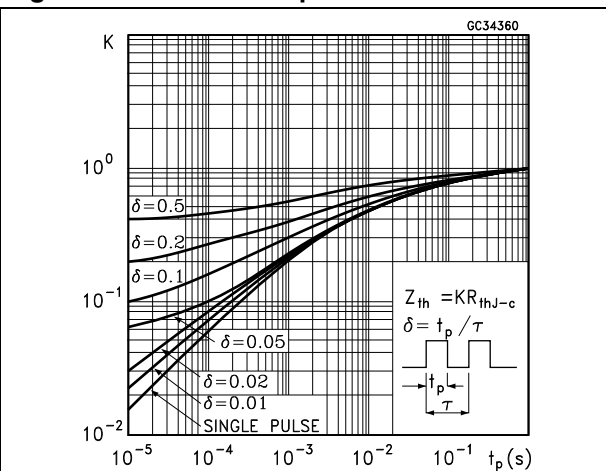


Figure 4. Safe operating area for TO-220

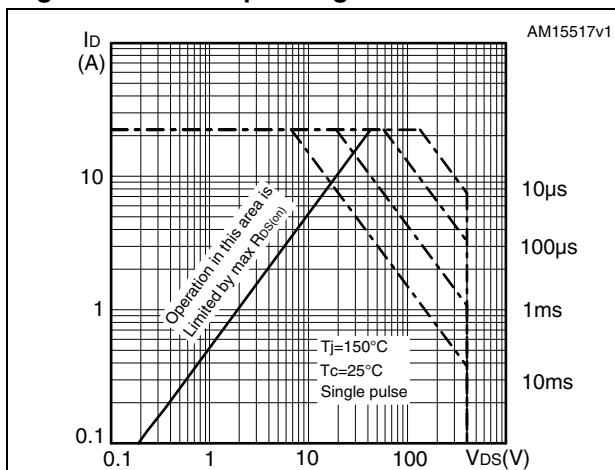


Figure 5. Thermal impedance for TO-220

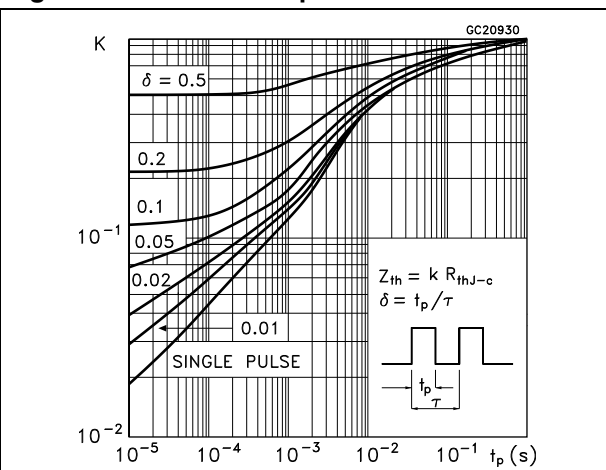


Figure 6. Output characteristics

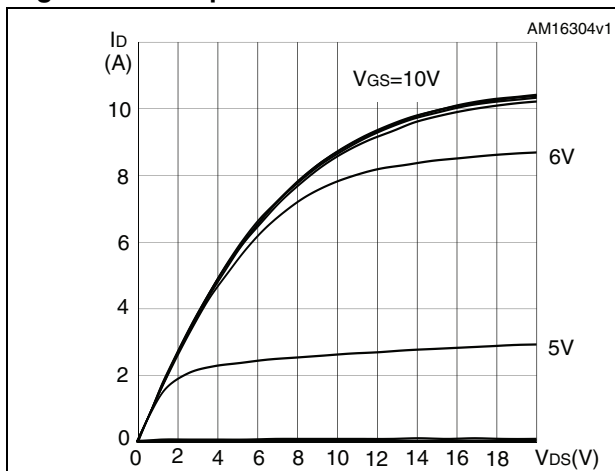


Figure 7. Transfer characteristics

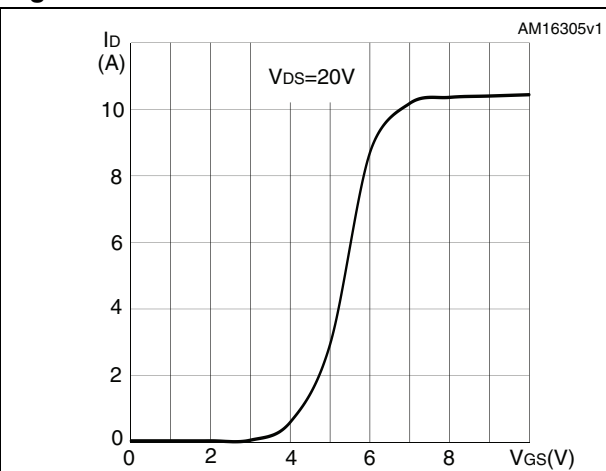


Figure 8. Static drain-source on-resistance

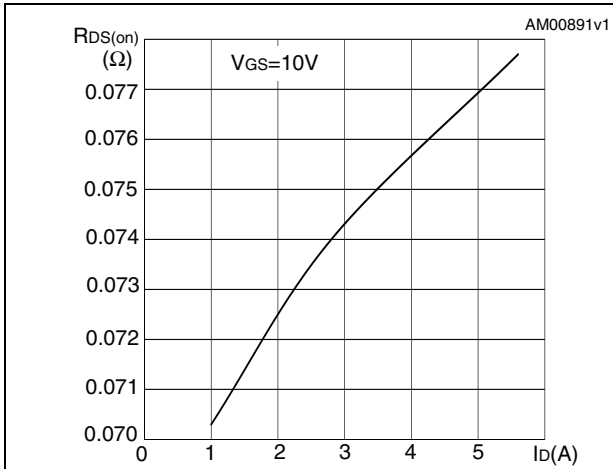


Figure 9. Gate charge vs gate-source voltage

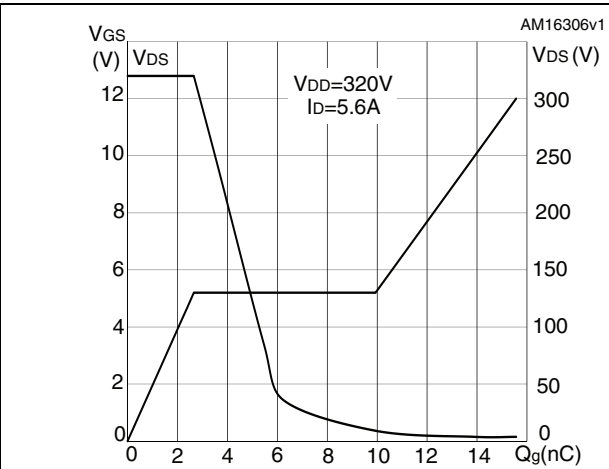


Figure 10. Capacitance variations

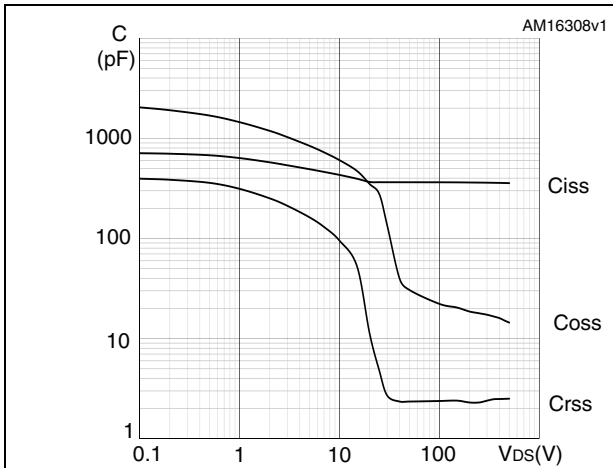


Figure 11. Output capacitance stored energy

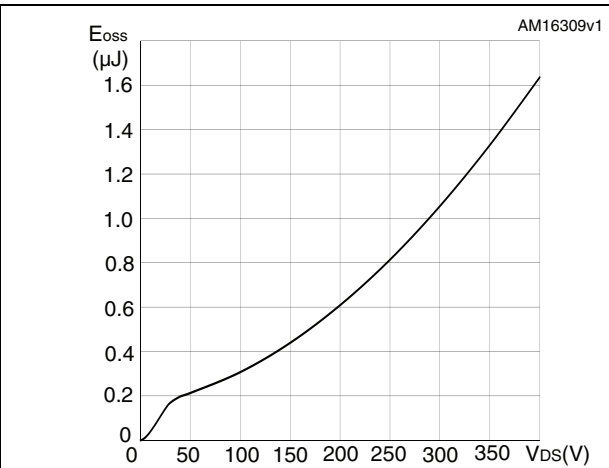


Figure 12. Normalized gate threshold voltage vs temperature

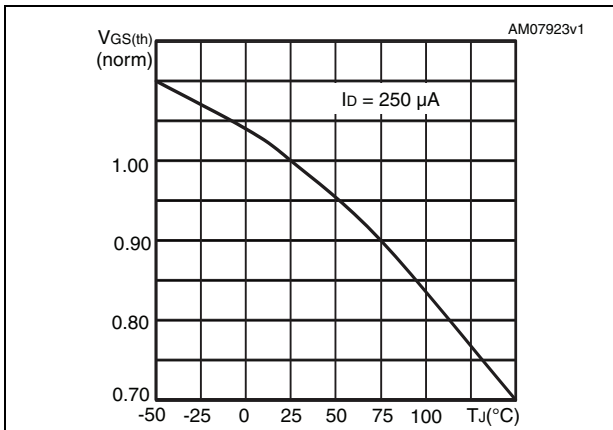


Figure 13. Normalized on resistance vs temperature

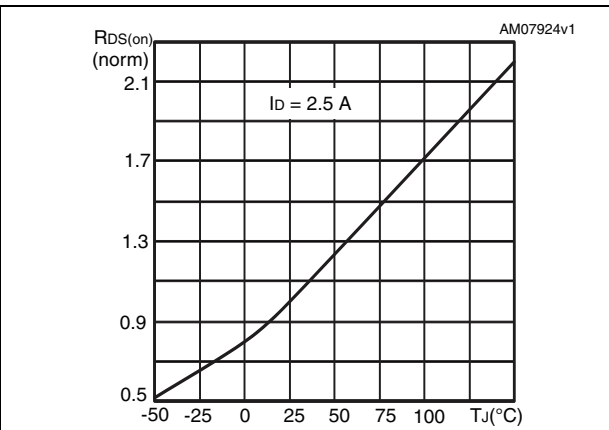


Figure 14. Normalized  $V_{DS}$  vs temperature

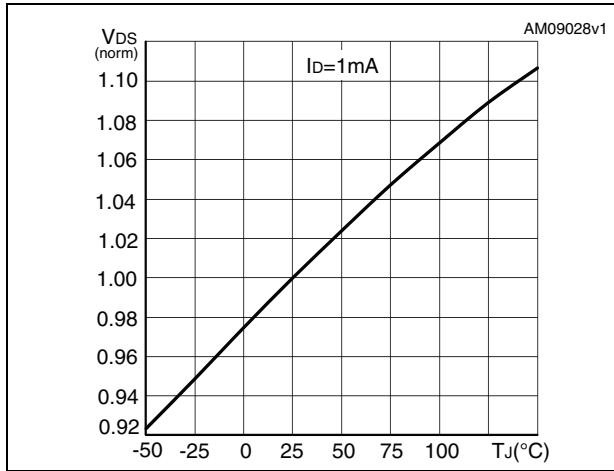
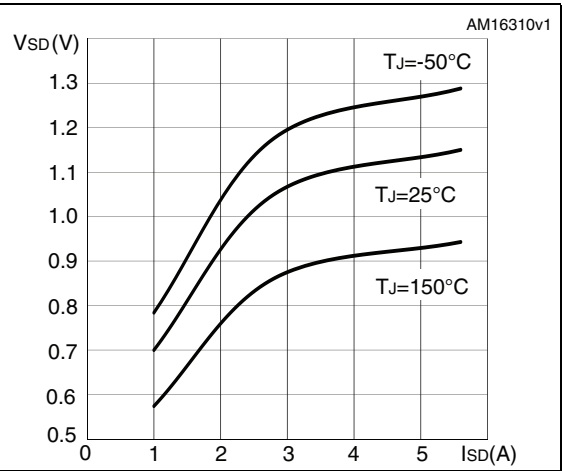


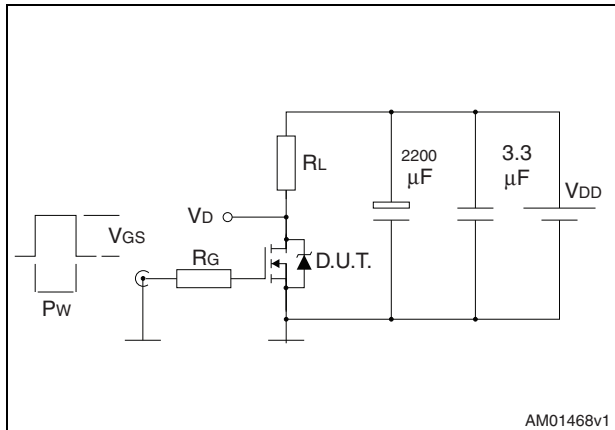
Figure 15. Source-drain diode forward characteristics





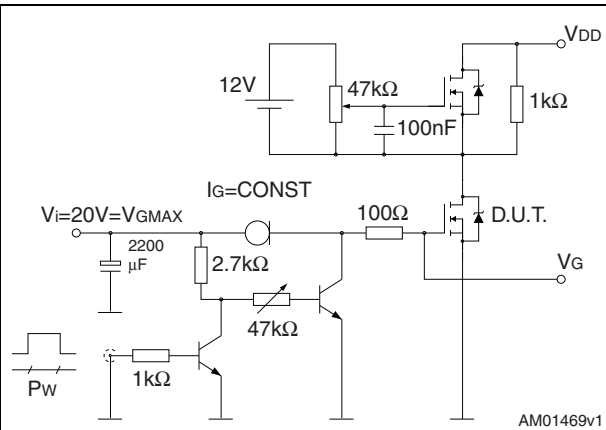
### 3 Test circuits

Figure 16. Switching times test circuit for resistive load



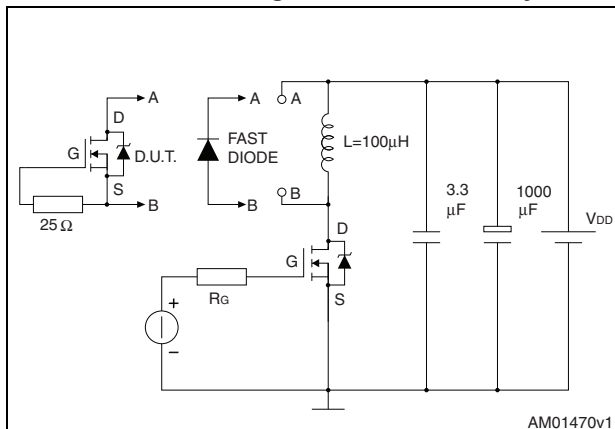
AM01468v1

Figure 17. Gate charge test circuit



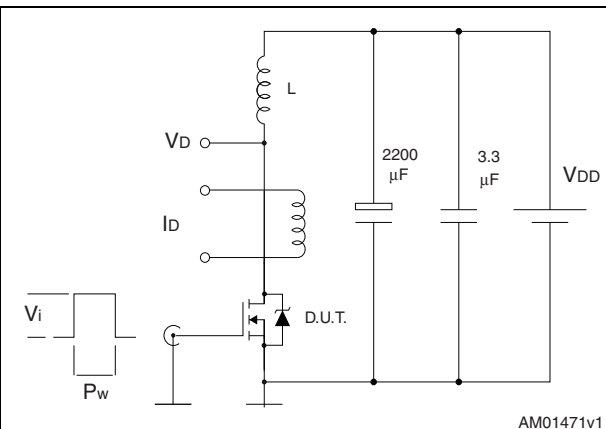
AM01469v1

Figure 18. Test circuit for inductive load switching and diode recovery times



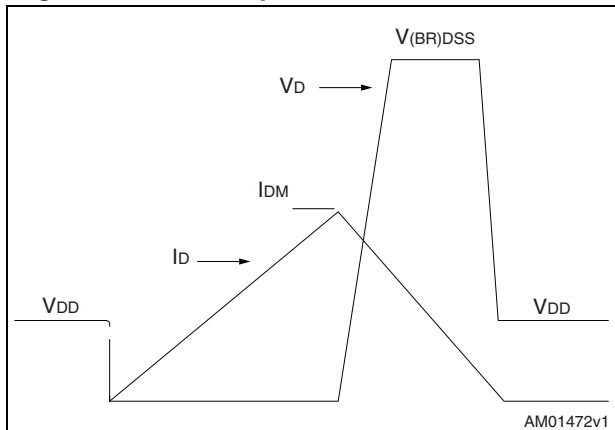
AM01470v1

Figure 19. Unclamped inductive load test circuit



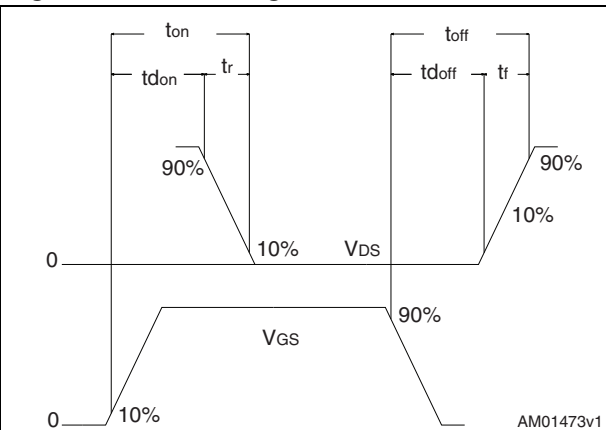
AM01471v1

Figure 20. Unclamped inductive waveform



AM01472v1

Figure 21. Switching time waveform



AM01473v1

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Table 9. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 22. DPAK (TO-252) drawing

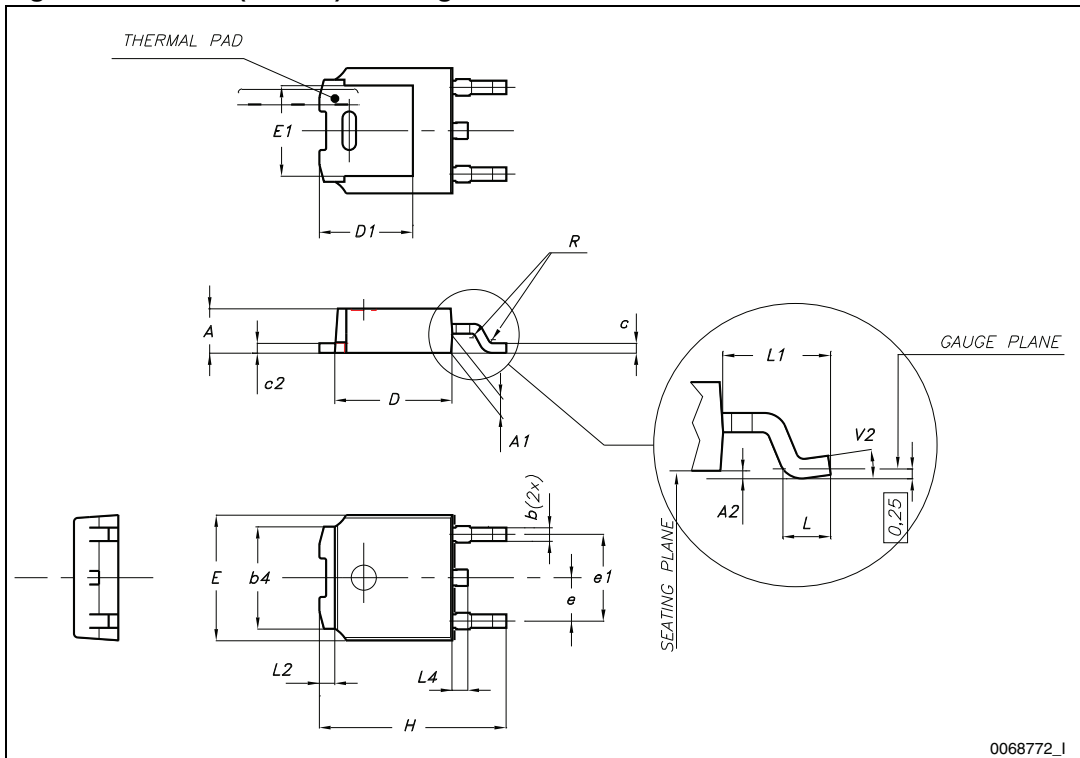
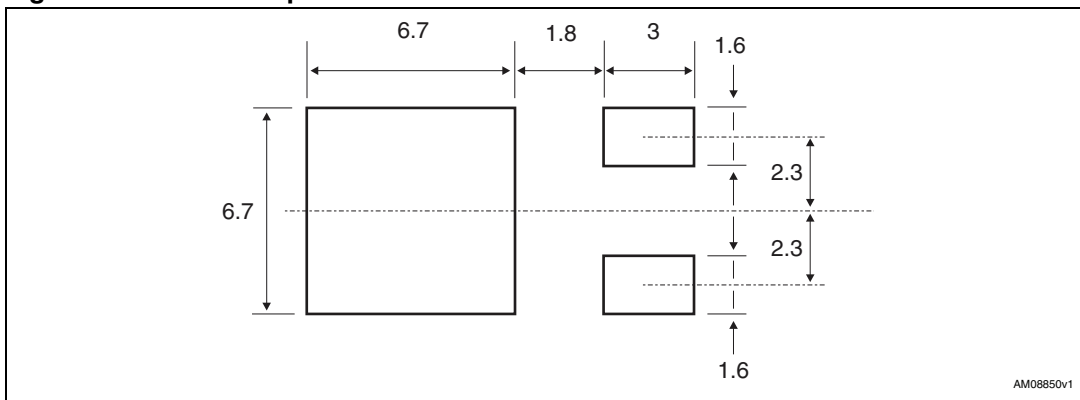


Figure 23. DPAK footprint<sup>(a)</sup>

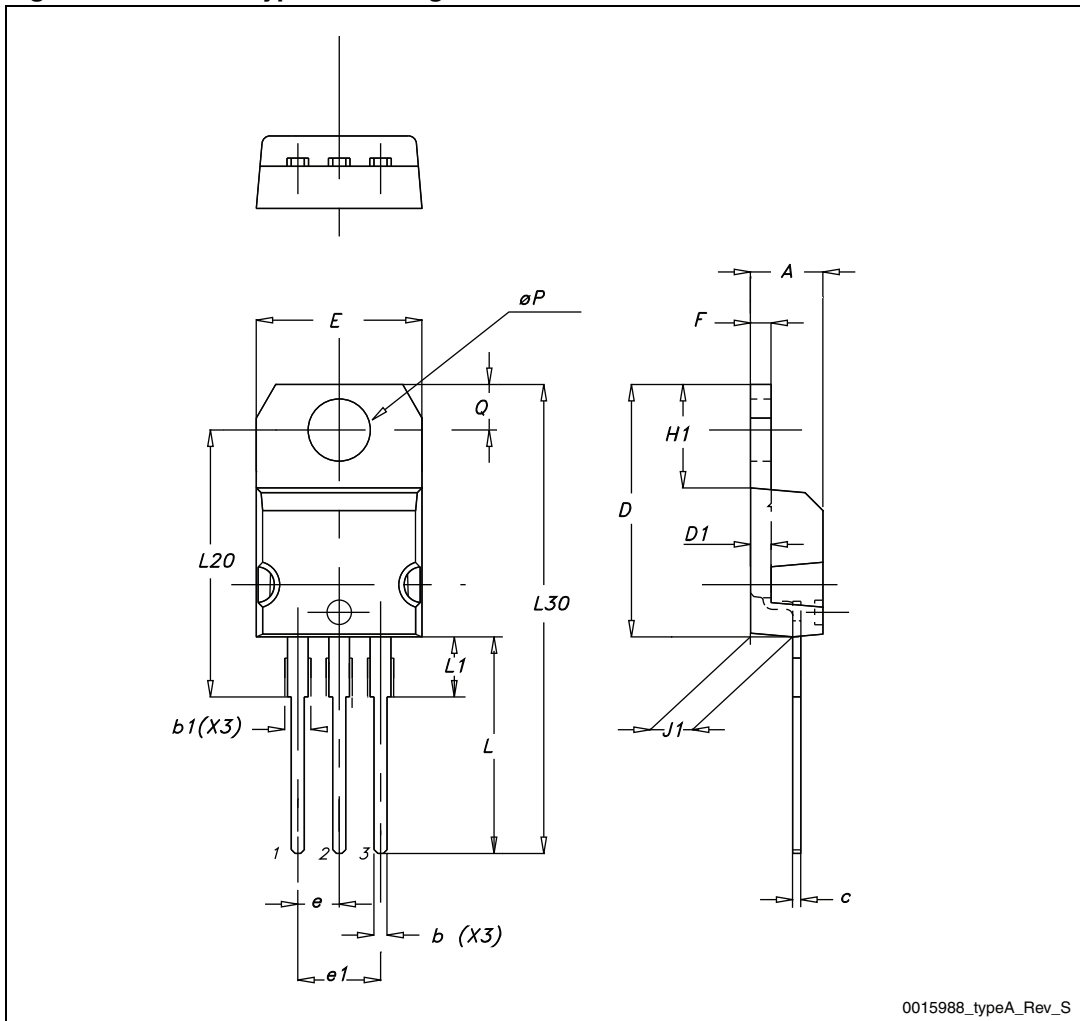


a. All dimensions are in millimeters

Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 24. TO-220 type A drawing



## 5 Packaging mechanical data

Table 11. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 25. Tape for DPAK (TO-252)

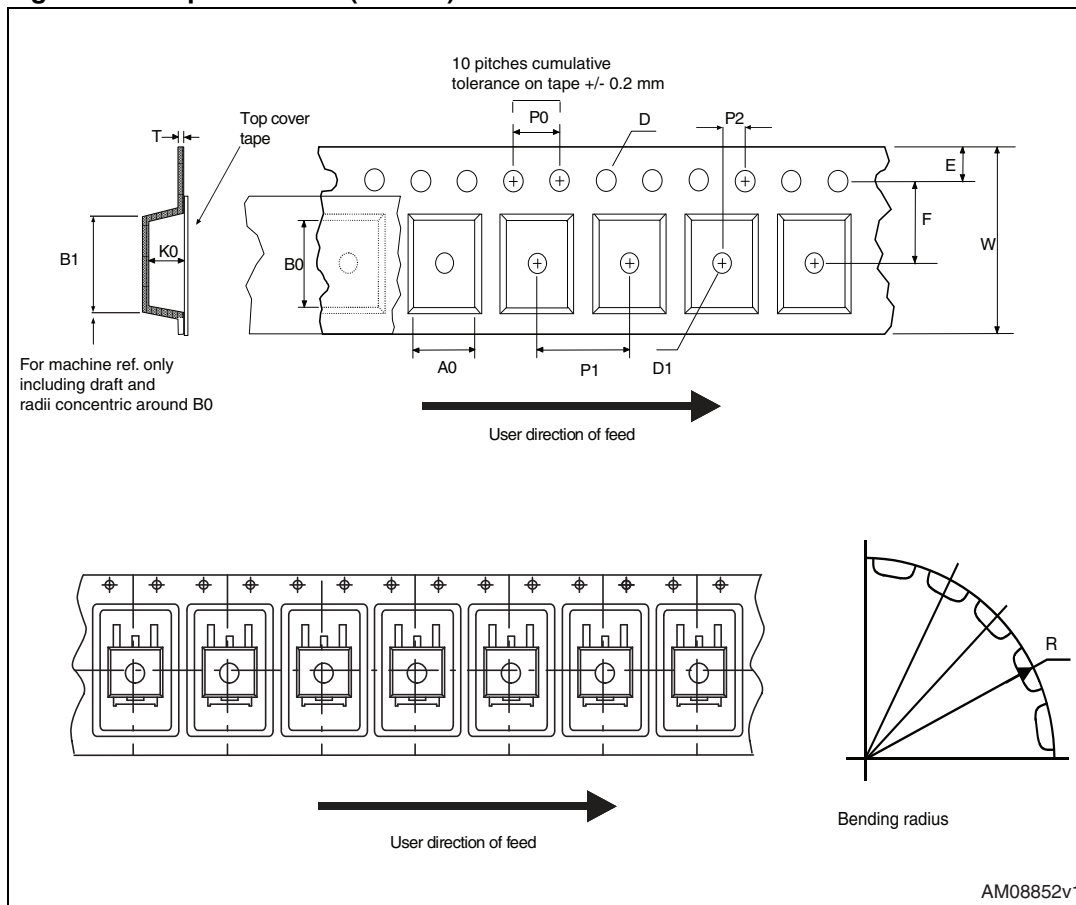
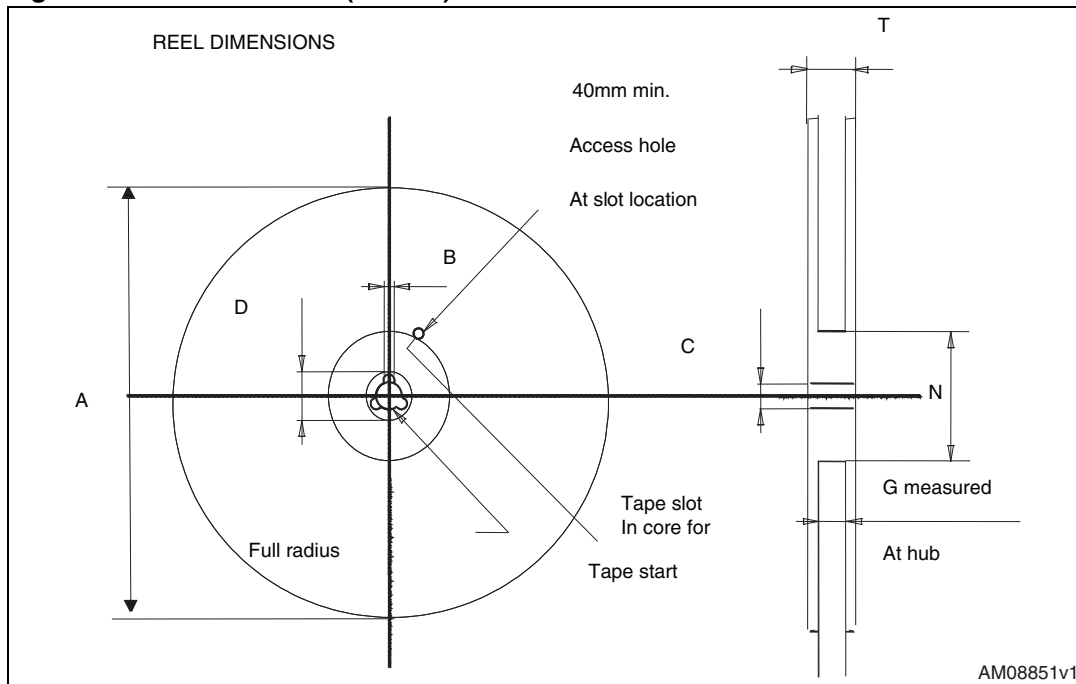


Figure 26. Reel for DPAK (TO-252)





## 6 Revision history

**Table 12. Document revision history**

Date	Revision	Changes
08-Oct-2012	1	First release.
14-Dec-2012	2	– Minor text changes – Added: TO-220 package

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